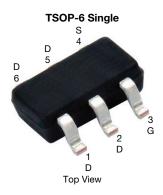


Vishay Siliconix

# Automotive P-Channel 60 V (D-S) 175 °C MOSFET



PRODUCT SUMMARY				
V <sub>DS</sub> (V)	-60			
$R_{DS(on)}$ ( $\Omega$ ) at $V_{GS} = -10 \text{ V}$	0.095			
$R_{DS(on)}$ ( $\Omega$ ) at $V_{GS} = -4.5 \text{ V}$	0.135			
I <sub>D</sub> (A)	-5.3			
Configuration	Single			

Marking Code: 9Q

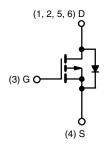
#### **FEATURES**

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % R<sub>q</sub> and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912





ROHS COMPLIANT HALOGEN FREE



P-Channel MOSFET

ORDERING INFORMATION	
Package	TSOP-6
Lead (Pb)-free and halogen-free	SQ3427CEV (for detailed order number please see <a href="https://www.vishay.com/doc?79771">www.vishay.com/doc?79771</a> )

ABSOLUTE MAXIMUM RATINGS (T <sub>C</sub> = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	LIMIT	UNIT			
Drain-Source Voltage	V <sub>DS</sub>	-60	V			
Gate-Source Voltage	$V_{GS}$	± 20	V			
Continuous Drain Current	T <sub>C</sub> = 25 °C	1	-5.3			
Continuous Drain Current	T <sub>C</sub> = 125 °C	- I <sub>D</sub>	-3			
Continuous Source Current (Diode Conduction	Is	-6.3	Α			
Pulsed Drain Current <sup>a</sup>	I <sub>DM</sub>	-21				
Single Pulse Avalanche Current	L = 0.1 mH	I <sub>AS</sub>	-21			
Single Pulse Avalanche Energy	L = 0.1 mm	E <sub>AS</sub>	22	mJ		
Maximum Power Dissipation	T <sub>C</sub> = 25 °C	P <sub>D</sub>	5	W		
	T <sub>C</sub> = 125 °C	L <sub>D</sub>	1.6	VV		
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C		

THERMAL RESISTANCE RATINGS						
PARAMETER	SYMBOL	LIMIT	UNIT			
Junction-to-Ambient	PCB Mount b	$R_{thJA}$	110	°C/W		
Junction-to-Foot (Drain)		$R_{thJF}$	30	C/VV		

#### Notes

- a. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%.$
- b. When mounted on 1" square PCB (FR4 material).



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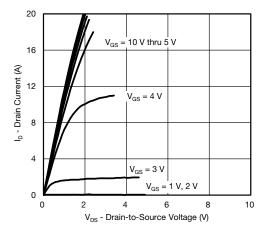
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static					•		
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0, I_D = -250 \mu\text{A}$		-60	-	-	V
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} =$	V <sub>GS</sub> , I <sub>D</sub> = -250 μA	-1.5	-2	-2.5	V
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	$0 \text{ V}, \text{ V}_{GS} = \pm 20 \text{ V}$	-		± 100	nA
		$V_{GS} = 0 V$	V <sub>DS</sub> = -60 V	-	-	-1	μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = -60 V, T <sub>J</sub> = 125 °C	-	-	-50	
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = -60 V, T <sub>J</sub> = 175 °C	-	-	-150	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = -10 V	$V_{DS} \le -5 \text{ V}$	-10	-	-	Α
		V <sub>GS</sub> = -10 V	I <sub>D</sub> = -4.5 A	-	0.079	0.095	
Drain Caures On State Resistance 3	В	V <sub>GS</sub> = -10 V	I <sub>D</sub> = -4.5 A, T <sub>J</sub> = 125 °C	-	-	0.148	Ω
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = -10 V	I <sub>D</sub> = -4.5 A, T <sub>J</sub> = 175 °C	-	-	0.178	
		V <sub>GS</sub> = -4.5 V	I <sub>D</sub> = -3.5 A	-	0.112	0.135	
Forward Transconductance <sup>a</sup>	g <sub>fs</sub>	V <sub>DS</sub> =	= -15 V, I <sub>D</sub> = -4 A	-	9	-	S
Dynamic <sup>b</sup>							
Input Capacitance	C <sub>iss</sub>		V <sub>DS</sub> = -30 V, f = 1 MHz	-	726	1000	pF
Output Capacitance	Coss	$V_{GS} = 0 V$		-	91	120	
Reverse Transfer Capacitance	C <sub>rss</sub>	1		-	56	80	
Total Gate Charge c	Qg				16.9	22	
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	V <sub>GS</sub> = -10 V	$V_{DS} = -30 \text{ V}, I_{D} = -5 \text{ A}$	-	2.9	-	nC
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$	1		-	4.1	-	
Gate Resistance	R <sub>g</sub>		f = 1 MHz	2.5	5	7.5	Ω
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			-	8	12	
Rise Time <sup>c</sup>	t <sub>r</sub>	V <sub>DD</sub> =	$V_{DD} = -30 \text{ V}, R_1 = 6 \Omega$		24	35	- ns
Turn-Off Delay Time c	t <sub>d(off)</sub>	$I_D \cong -5$ Å, $V_{GEN} = -10$ V, $R_g = 1$ $\Omega$		-	25	38	
Fall Time <sup>c</sup>	t <sub>f</sub>			-	33	50	
Source-Drain Diode Ratings and Characte	ristics <sup>b</sup>						
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	-21	Α
Forward Voltage	$V_{SD}$	I <sub>F</sub> = -1.6 A, V <sub>GS</sub> = 0 V		-	-0.8	-1.2	V
Body diode reverse recovery time	t <sub>rr</sub>			-	23	46	ns
Body diode reverse recovery charge	Q <sub>rr</sub>	I <sub>F</sub> = -1.7 A, di/dt = 100 A/μs		-	27	54	<sub>2</sub> 0
Reverse recovery fall time	ta			-	20	-	nC
Reverse recovery rise time	t <sub>b</sub>			-	3	-	ns
Body diode peak reverse recovery current	I <sub>RM(REC)</sub>			1	-2.86	-	Α

#### Notes

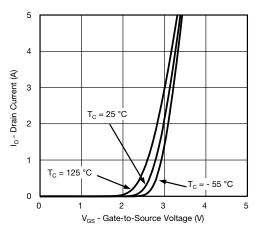
- a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

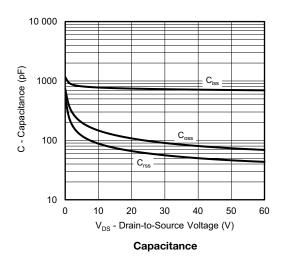


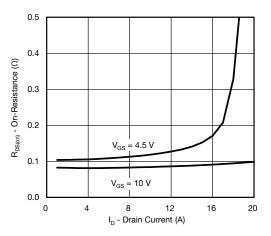


#### **Output Characteristics**

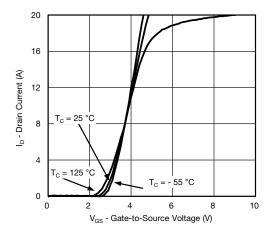


**Transfer Characteristics** 

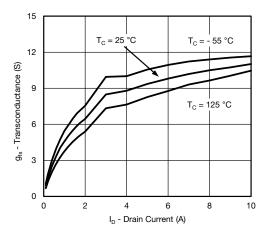




On-Resistance vs. Drain Current and Gate Voltage

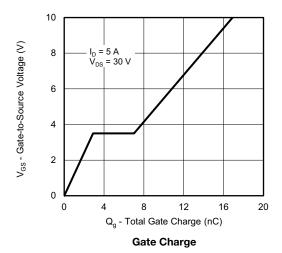


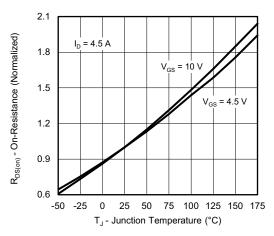
**Transfer Characteristics** 



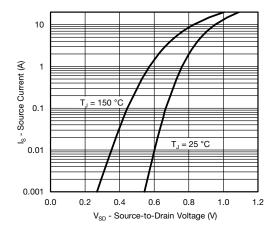
Transconductance



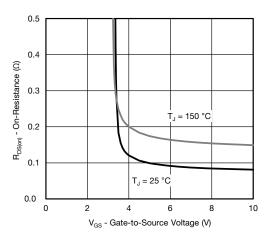




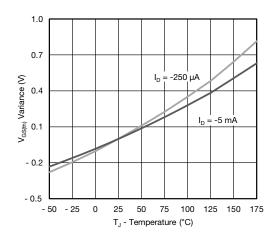
On-Resistance vs. Junction Temperature



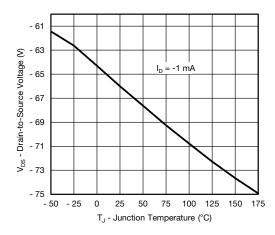
Source-Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage

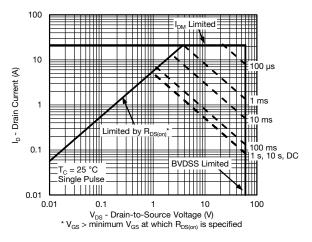


Threshold Voltage

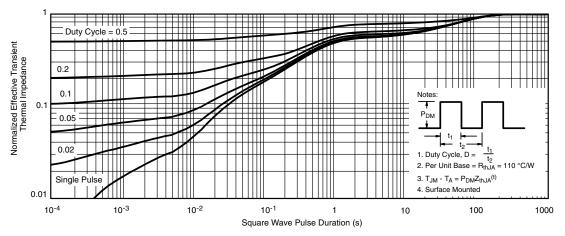


**Drain-to-Source Voltage vs. Junction Temperature** 



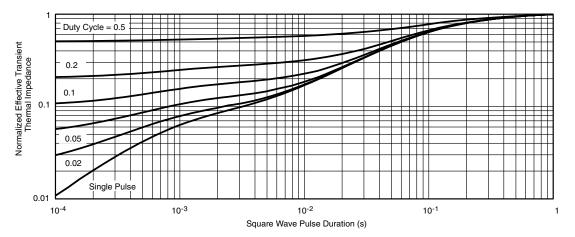


Safe Operating Area, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Ambient





Normalized Thermal Transient Impedance, Junction-to-Foot

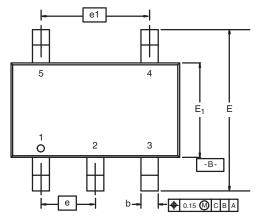
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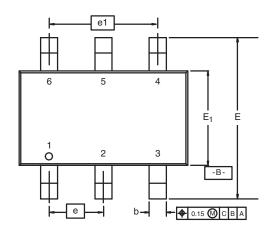




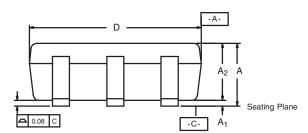
TSOP: 5/6-LEAD

**JEDEC Part Number: MO-193C** 

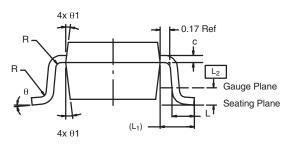




**5-LEAD TSOP** 





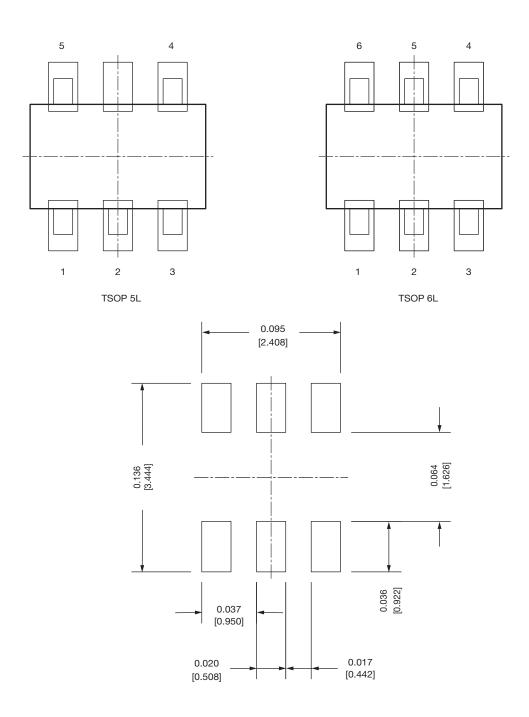


	MIL	LIMETER	RS	INCHES			
Dim	Min	Nom	Max	Min	Nom	Max	
Α	0.91	-	1.10	0.036	-	0.043	
A <sub>1</sub>	0.01	-	0.10	0.0004	-	0.004	
A <sub>2</sub>	0.90	-	1.00	0.035	0.038	0.039	
b	0.30	0.32	0.45	0.012	0.013	0.018	
С	0.10	0.15	0.20	0.004	0.006	0.008	
D	2.95	3.05	3.10	0.116	0.120	0.122	
E	2.70	2.85	2.98	0.106	0.112	0.117	
E <sub>1</sub>	1.55	1.65	1.70	0.061	0.065	0.067	
е		0.95 BSC		0.0374 BSC			
e <sub>1</sub>	1.80	1.90	2.00	0.071	0.075	0.079	
L	0.32	-	0.50	0.012	-	0.020	
L <sub>1</sub>		0.60 Ref		0.024 Ref			
L <sub>2</sub>		0.25 BSC			0.010 BSC		
R	0.10	-	-	0.004	-	-	
θ	0°	4°	8°	0°	4°	8°	
θ1	7° Nom			7° Nom			
ECN: C-06593-Rev. I, 18-Dec-06 DWG: 5540							

Document Number: 71200 18-Dec-06



## Recommended Land Pattern For TSOP-5L / TSOP-6L



#### Note

• All dimensions are in inches (millimeter)

ECN: C22-0860-Rev. B, 24-Oct-2022 DWG: 3010



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